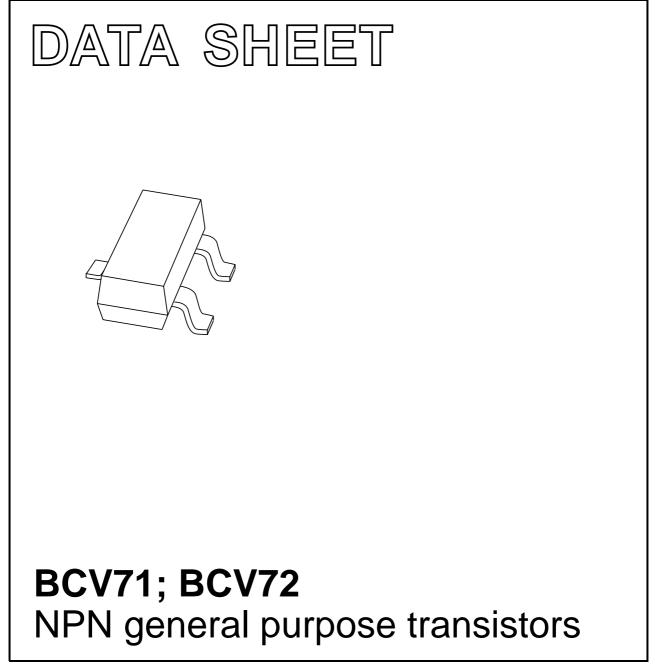
# DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 1997 Mar 11 1999 Apr 08



# NPN general purpose transistors

### FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 60 V).

### APPLICATIONS

• General purpose switching and amplification.

### DESCRIPTION

NPN transistor in a SOT23 plastic package.

#### MARKING

TYPE NUMBER	MARKING CODE <sup>(1)</sup>
BCV71	K7*
BCV72	K8*

#### Note

1. \* = p : Made in Hong Kong.

\* = t : Made in Malaysia.

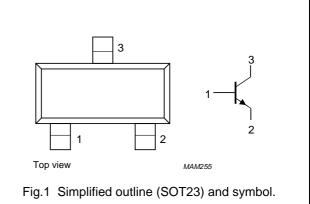
### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	-	80	V
V <sub>CEO</sub>	collector-emitter voltage	open base; I <sub>C</sub> = 2 mA	-	60	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	5	V
I <sub>C</sub>	collector current (DC)		-	100	mA
I <sub>CM</sub>	peak collector current		-	200	mA
I <sub>BM</sub>	peak base current		-	200	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	-	250	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C



PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	



# **BCV71; BCV72**

# NPN general purpose transistors

# BCV71; BCV72

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT	
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	500	K/W	

### Note

1. Transistor mounted on an FR4 printed-circuit board.

### CHARACTERISTICS

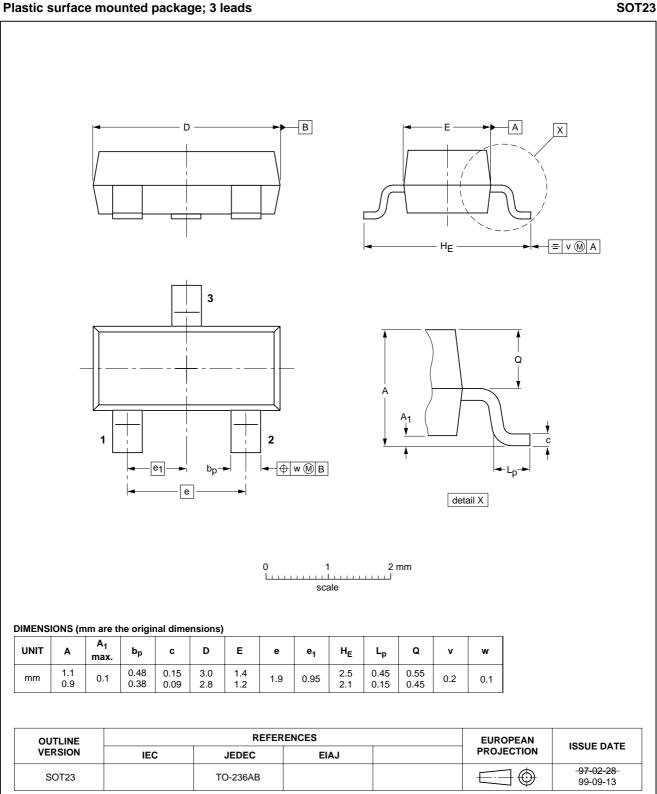
 $T_i = 25 \ ^{\circ}C$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector cut-off current	I <sub>E</sub> = 0; V <sub>CB</sub> = 20 V	-	-	100	nA
		I <sub>E</sub> = 0; V <sub>CB</sub> = 20 V; T <sub>j</sub> = 100 °C	-	—	10	μA
I <sub>EBO</sub>	emitter cut-off current	I <sub>C</sub> = 0; V <sub>EB</sub> = 5 V	-	_	100	nA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> = 10 μA; V <sub>CE</sub> = 5 V				
	BCV71		-	90	_	
	BCV72		-	150	_	
	DC current gain	I <sub>C</sub> = 2 mA; V <sub>CE</sub> = 5 V				
	BCV71		110	_	220	
	BCV72		200	_	450	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 0.5 mA	-	120	250	mV
		$I_{\rm C} = 50 \text{ mA}; I_{\rm B} = 2.5 \text{ mA}$	-	210	_	mV
	base-emitter saturation voltage	$I_{\rm C} = 10 \text{ mA}; I_{\rm B} = 0.5 \text{ mA}$	-	750	_	mV
		$I_{\rm C} = 50 \text{ mA}; I_{\rm B} = 2.5 \text{ mA}$	-	850	_	mV
V <sub>BE</sub>	base-emitter voltage	I <sub>C</sub> = 2 mA; V <sub>CE</sub> = 5 V	550	_	700	mV
Cc	collector capacitance	I <sub>E</sub> = i <sub>e</sub> = 0; V <sub>CB</sub> = 10 V; f = 1 MHz	-	2.5	_	pF
f <sub>T</sub>	transition frequency	I <sub>C</sub> = 10 mA; V <sub>CE</sub> = 5 V; f = 100 MHz	100	_	_	MHz
F	noise figure	$      I_C = 200 \ \mu\text{A}; \ V_{CE} = 5 \ \text{V}; \ \text{R}_S = 2 \ \text{k}\Omega; \\      f = 1 \ \text{kHz}; \ \text{B} = 200 \ \text{Hz} $	-	_	10	dB

BCV71; BCV72

# NPN general purpose transistors

### **PACKAGE OUTLINE**



## NPN general purpose transistors

## BCV71; BCV72

#### DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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# **NXP Semiconductors**

#### **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

#### **Contact information**

For additional information please visit: http://www.nxp.com For sales offices addresses send e-mail to: salesaddresses@nxp.com

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